Tatsuya Usuki

List of Publications by Year
in descending order

92 papers	2,182 citations	218677 26 h-index	233421 45 g-index
93 all docs	93 docs citations	93 times ranked	1735 citing authors

#	Article	IF	Citations
1	Error-Free Operation for Fully Connected Wavelength-Routing Interconnect among 8 FPGAs with 2.8-Tbit/s Total Bandwidth. , 2021, , .		0
2	Wavelength-routing interconnect "Optical Hub" for parallel computing systems. , 2020, , .		4
3	Numerical Designing of Optical Waveguide by Curvilinear Coordinates. , 2019, , .		0
4	Ultralow-Power (1.59 mW/Gbps), 56-Gbps PAM4 Operation of Si Photonic Transmitter Integrating Segmented PIN Machâ€"Zehnder Modulator and 28-nm CMOS Driver. Journal of Lightwave Technology, 2018, 36, 1275-1280.	4.6	41
5	Accurate SPICE Model of Forward-Biased Silicon PIN Machâ€"Zehnder Modulator for an Energy-Efficient Multilevel Transmitter. Journal of Lightwave Technology, 2018, 36, 1959-1969.	4.6	13
6	Ultra-Low-Power (1.59 mW/Gbps), 56-Gbps PAM4 Operation of Si Photonic Transmitter Integrating Segmented PIN Mach-Zehnder Modulator and 28-nm CMOS Driver. , 2017, , .		2
7	Numerical simulation of waveguide light scattering for Si photonics. , 2017, , .		0
8	25-Gb/s broadband silicon modulator with 031-VÂ·cm VÏ€L based on forward-biased PIN diodes embedded with passive equalizer. Optics Express, 2015, 23, 32950.	3.4	13
9	Bit error rate analysis of a silicon optical interposer using its equivalent circuit. IEICE Electronics Express, 2015, 12, 20141084-20141084.	0.8	1
10	Athermal silicon optical interposers operating up to 125Â° C. Proceedings of SPIE, 2015, , .	0.8	0
11	First Demonstration of Athermal Silicon Optical Interposers With Quantum Dot Lasers Operating up to 125 Â°C. Journal of Lightwave Technology, 2015, 33, 1223-1229.	4.6	106
12	High-speed and efficient silicon modulator based on forward-biased pin diodes. Frontiers in Physics, 2014, 2, .	2.1	20
13	Demonstration of 25-Gbps optical data links on silicon optical interposer using FPGA transceiver. , 2014, , .		4
14	High-performance silicon modulator for integrated transceivers fabricated on 300-mm wafer. , 2014, , .		3
15	Athermal silicon optical interposers with quantum dot lasers operating from 25 to 125Â°C. Electronics Letters, 2014, 50, 1377-1378.	1.0	0
16	High-density optical interconnects by using silicon photonics. Proceedings of SPIE, 2014, , .	0.8	8
17	High-density and wide-bandwidth optical interconnects with silicon optical interposers [Invited]. Photonics Research, 2014, 2, A1.	7.0	40
18	Fully Integrated Silicon Optical Interposers with High Bandwidth Density. , 2014, , .		0

#	Article	IF	Citations
19	Compact PIN-Diode-Based Silicon Modulator Using Side-Wall-Grating Waveguide. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 74-84.	2.9	43
20	50-Gb/s ring-resonator-based silicon modulator. Optics Express, 2013, 21, 11869.	3.4	165
21	Advances in High-Density Inter-Chip Interconnects with Photonic Wiring. IEICE Transactions on Electronics, 2013, E96.C, 958-965.	0.6	1
22	High-density Silicon Optical Interposer for Inter-chip Interconnects based on Compact and High Speed Components. , 2013, , .		2
23	Silicon-Wire Waveguide Based External Cavity Laser for Milliwatt-Order Output Power and Temperature Control Free Operation with Silicon Ring Modulator. Japanese Journal of Applied Physics, 2012, 51, 082101.	1.5	1
24	125-Gb/s operation with 029-VÂ·cm V_Ï€L using silicon Mach-Zehnder modulator based-on forward-biased pin diode. Optics Express, 2012, 20, 2911.	3.4	62
25	Demonstration of 125-Gbps optical interconnects integrated with lasers, optical splitters, optical modulators and photodetectors on a single silicon substrate. Optics Express, 2012, 20, B256.	3.4	53
26	Cascaded-ring-resonator-loaded Machâ€“Zehnder modulator for enhanced modulation efficiency in wide optical bandwidth. Optics Express, 2012, 20, 16321.	3.4	15
27	Demonstration of 12.5-Gbps Optical Interconnects Integrated with Lasers, Optical Splitters, Optical Modulators and Photodetectors on a Single Silicon Substrate. , 2012, , .		4
28	Robust Optical Data Transfer on Silicon Photonic Chip. Journal of Lightwave Technology, 2012, 30, 2933-2940.	4.6	10
29	Silicon-Wire Waveguide Based External Cavity Laser for Milliwatt-Order Output Power and Temperature Control Free Operation with Silicon Ring Modulator. Japanese Journal of Applied Physics, 2012, 51, 082101.	1.5	3
30	Hybrid laser with Si ring resonator and SOA for temperature control free operation with ring resonator-based modulator. , 2011, , .		2
31	Differential signal transmission in silicon-photonics integrated circuit for high density optical interconnects. , 2011, , .		4
32	First demonstration of high density optical interconnects integrated with lasers, optical modulators, and photodetectors on single silicon substrate. Optics Express, 2011, 19, B159.	3.4	90
33	First Demonstration of High Density Optical Interconnects Integrated with Lasers, Optical Modulators and Photodetectors on a Single Silicon Substrate. , 2011, , .		4
34	Slow-Light Silicon Mach-Zehnder Modulator Based-on Cascaded Ring Resonators. , 2010, , .		3
35	Transmission Experiment of Quantum Keys over 50 km Using High-Performance Quantum-Dot Single-Photon Source at 1.5 Âµm Wavelength. Applied Physics Express, 2010, 3, 092802.	2.4	58
36	A 1 V Peak-to-Peak Driven 10-Gbps Slow-Light Silicon Machâ€“Zehnder Modulator Using Cascaded Ring Resonators. Applied Physics Express, 2010, 3, 072202.	2.4	28

#	Article	IF	Citations
37	Tunneling-Injection Single-Photon Emitter Using Charged Exciton State. Japanese Journal of Applied Physics, 2009, 48, 06FF01.	1.5	0
38	Decoherence of single photons from an InAs/InP quantum dot emitting at a 1.3 Î¼m wavelength. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 944-947.	0.8	4
39	Sub-GHz operation of single-photon emitting diode at 1.55 Î¼m. Proceedings of SPIE, 2009, , .	0.8	2
40	Exciton dynamics in current-injected single quantum dot at 1.55Î¼m. Applied Physics Letters, 2008, 92, 161104.	3.3	17
41	Laterally coupled self-assembled InAs quantum dots embedded in resonant tunnel diode with multigate electrodes. Applied Physics Letters, 2008, 92, .	3.3	35
42	First Demonstration of Electrically Driven 1.55 Âµm Single-Photon Generator. Japanese Journal of Applied Physics, 2008, 47, 2880-2883.	1.5	25
43	Electric field modulation of exciton recombination in InAs/GaAs quantum dots emitting at 1.3Î¼m. Journal of Applied Physics, 2008, 104, 013504.	2.5	6
44	Studies of Semiconductor Quantum Dots for Quantum Information Processing. , 2008, , 267-296.		0
45	An optical horn structure for single-photon source using quantum dots at telecommunication wavelength. Journal of Applied Physics, 2007, 101, 081720.	2.5	93
46	Single-photon interferography in InAsâˆ•InP quantum dots emitting at 1300nm wavelength. Applied Physics Letters, 2007, 91, 223113.	3.3	10
47	Radiative recombination of excitons in disk-shaped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">As</mml:mi><mml:mo>âˆ•</mml:mo><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">P</mml:mi></mml:mrow></mml:math>quantum dots. Physical Review B, 2007, 76, .	3.2	14
48	Sharp Interfacial Structure of InAs/InP Quantum Dots Grown by a Double-Cap Method: A Cross-Sectional Scanning Tunneling Microscopy Study. AIP Conference Proceedings, 2007, , .	0.4	0
49	First Demonstration of Electrically Driven 1.55 Î¼m Single-Photon Generator. , 2007, , .		0
50	Triggered single-photon emission and cross-correlation properties in InAlAs quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 144-147.	2.7	9
51	Site-controlled quantum dots fabricated using an atomic-force microscope assisted technique. Nanoscale Research Letters, 2006, 1, 160-166.	5.7	19
52	Development of Electrically Driven Single-Quantum-Dot Device at Optical Fiber Bands. Japanese Journal of Applied Physics, 2006, 45, 3621-3624.	1.5	13
53	Mechanism of Quantum Dot Formation by Postgrowth Annealing of Wetting Layer. Japanese Journal of Applied Physics, 2006, 45, 3564-3567.	1.5	1
54	Single-photon generator for telecom applications. , 2006, , .		0

#	Article	IF	Citations
55	Controlling emission wavelength from InAs self-assembled quantum dots on InP (001) during MOCVD. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 81-85.	2.7	19
56	Single InAs/InP quantum dot spectroscopy in 1.3â€"1.55Î¼m telecommunication band. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 185-189.	2.7	11
57	Observation of Overhauser shift in a self-assembled InAlAs quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 29, 510-514.	2.7	7
58	Single-photon generation from InAlAs single quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3833-3837.	0.8	6
59	Photon Antibunching Observed from an InAlAs Single Quantum Dot. Japanese Journal of Applied Physics, 2005, 44, L793-L796.	1.5	24
60	Site-controlled photoluminescence at telecommunication wavelength from InAsâˆ•InP quantum dots. Applied Physics Letters, 2005, 86, 113118.	3.3	54
61	Few-Electron Molecular States and Their Transitions in a Single InAs Quantum Dot Molecule. Physical Review Letters, 2005, 95, 236801.	7.8	25
62	Polarization-dependent shift in excitonic Zeeman splitting of self-assembledIn0.75Al0.25Asâˆ•Al0.3Ga0.7Asquantum dots. Physical Review B, 2005, 71, .	3.2	40
63	Single-Photon Generation in the 1.55-Âµm Optical-Fiber Band from an InAs/InP Quantum Dot. Japanese Journal of Applied Physics, 2005, 44, L620-L622.	1.5	120
64	Development of Electrically Driven Single-Photon Emitter at Optical Fiber Bands. , 2005, , .		0
65	Coulomb interaction in asymmetric triple-coupled quantum dots. Semiconductor Science and Technology, 2004, 19, S409-S411.	2.0	5
66	Spin Depolarization via Tunneling Effects in Asymmetric Double Quantum Dot Structure. Japanese Journal of Applied Physics, 2004, 43, 2110-2113.	1.5	23
67	Scanning tunneling microscope study of capped quantum dots. Applied Physics Letters, 2004, 85, 2355-2357.	3.3	4
68	Observation of electrostatically released DNA from gold electrodes with controlled threshold voltages. Journal of Chemical Physics, 2004, 120, 5501-5504.	3.0	44
69	Non-classical Photon Emission from a Single InAs/InP Quantum Dot in the 1.3-Âµm Optical-Fiber Band. Japanese Journal of Applied Physics, 2004, 43, L993-L995.	1.5	71
70	Observation of Exciton Transition in 1.3-1.55 Âµm Band from Single InAs/InP Quantum Dots in Mesa Structure. Japanese Journal of Applied Physics, 2004, 43, L349-L351.	1.5	47
71	Metal Oxide Semiconductor Field Effect Transistor (MOSFET) Model Based on a Physical High-Field Carrier-Velocity Model. Japanese Journal of Applied Physics, 2004, 43, 77-81.	1.5	5
72	Advantage of a Quasi-Nonvolatile Memory with Ultra Thin Oxide. , 2001, , .		0

#	Article	IF	Citations
73	A direct tunneling memory using ultra-thin oxide and deca-nano floating gate structure. Superlattices and Microstructures, 2000, 28, 401-406.	3.1	0
74	Trade-off between operational speed and error occurrence for single electron circuits on the quantum scale. Microelectronic Engineering, 1999, 47, 269-271.	2.4	1
75	A proposal of new floating-dot memory storing a small number of electrons with relatively long retention time at low voltage operations. Microelectronic Engineering, 1999, 47, 281-283.	2.4	17
76	Theoretical Analysis of Write Errors and Number of Stored Electrons for Ten-Nanoscale Si Floating-Dot Memory. Japanese Journal of Applied Physics, 1998, 37, L709-L711.	1.5	3
77	Microstructure and electrical properties of Sn nanocrystals in thin, thermally grown SiO2 layers formed via low energy ion implantation. Journal of Applied Physics, 1998, 84, 1316-1320.	2.5	72
78	Analysis of Landau-Zener tunneling with an Ohmic reservoir and a noise source. Physical Review B, 1998, 57, 7124-7131.	3.2	6
79	Theoretical study of Landau-Zener tunneling at theM+Nlevel crossing. Physical Review B, 1997, 56, 13360-13366.	3.2	39
80	Numerical analysis of ballistic-electron transport in magnetic fields by using a quantum point contact and a quantum wire. Physical Review B, 1995, 52, 8244-8255.	3.2	157
81	Time-Resolved Study of Carrier Transfer among InAs/GaAs Multi-Coupled Quantum Dots. Japanese Journal of Applied Physics, 1995, 34, L1439.	1.5	34
82	Time-Resolved Study of Carrier Transfer among InAs/GaAs Multi-Coupled Quantum Dots. Japanese Journal of Applied Physics, 1995, 34, L1439-L1441.	1.5	34
83	InAs/GaAs Multi-Coupled Quantum Dots Structure Enabling High-Intensity, Near-1.3-Î¼m Emission due to Cascade Carrier Tunneling. , 1995, , .		0
84	Numerical analysis of electron-wave detection by a wedge-shaped point contact. Physical Review B, 1994, 50, 7615-7625.	3.2	29
85	Coupling between oneâ€dimensional states in a quantum point contact and an electron waveguide. Applied Physics Letters, 1994, 65, 3087-3089.	3.3	9
86	Thermodynamic Quantities of the One-Dimensional Hubbard Model at Finite Temperatures. Journal of the Physical Society of Japan, 1990, 59, 1357-1365.	1.6	57
87	Charge susceptibility of the one-dimensional Hubbard model. Physics Letters, Section A: General, Atomic and Solid State Physics, 1989, 135, 476-480.	2.1	67
88	Thermodynamic properties of the one-dimensional Hubbard model. Physics Letters, Section A: General, Atomic and Solid State Physics, 1989, 137, 287-290.	2.1	54
89	Magnetization Curve for Ce Compounds in the Crystalline Field. Journal of the Physical Society of Japan, 1989, 58, 1427-1432.	1.6	4
90	Magnetization curve for the heavy fermion compounds CeAl3 and CeCu2Si2. Journal of Magnetism and Magnetic Materials, 1988, 76-77, 121-122.	2.3	6

#	Article	IF	Citations
91	Thermoelectric Power of the Anderson Model at Low Temperatures. Journal of the Physical Society of Japan, 1987, 56, 1539-1545.	1.6	18
92	V/sub th/ fluctuation induced by statistical variation of pocket dopant profile. , 0, , .		19